

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D max $T_A = +25^\circ\text{C}$
20V	320m Ω @ $V_{GS} = 4.5\text{V}$	1.0A
	500m Ω @ $V_{GS} = 2.5\text{V}$	0.65A
	1000m Ω @ $V_{GS} = 1.8\text{V}$	0.4A

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Load switch

Features and Benefits

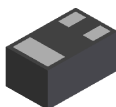
- Footprint of just 0.6mm² – thirteen times smaller than SOT23
- 0.4mm profile – ideal for low profile applications
- Low Gate Threshold Voltage
- Fast Switching Speed
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**
- ESD Protected Gate 2KV**

Mechanical Data

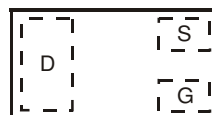
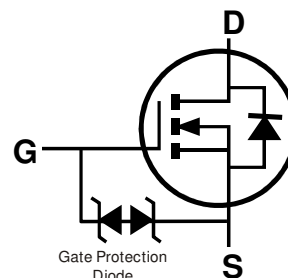
- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ⁽⁴⁾
- Weight: 0.001 grams (Approximate)



X2-DFN1006-3



Bottom View


Top View
Internal Schematic


Equivalent Circuit

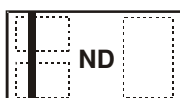
Ordering Information (Note 4)

Part Number	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN2320UFB4-7B	ND	7	8	10,000

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 - See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information

DMN2320UFB4-7B



ND = Product Type Marking Code

Top View
Bar Denotes Gate
and Source Side

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate-Source Voltage	V _{GSS}	±8	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	I _D	1.0 0.7	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)	I _{DM}	6	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P _D	0.52	W
Total Power Dissipation (Note 6)	P _D	1.07	W
Thermal Resistance, Junction to Ambient (Note 5)	R _{θJA}	240	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	R _{θJA}	117	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	-	-	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	1	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	10	μA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	0.50	-	0.95	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	-	320	mΩ	V _{GS} = 4.5V, I _D = 500mA
		-	-	500		V _{GS} = 2.5V, I _D = 400mA
		-	-	1,000		V _{GS} = 1.8V, I _D = 100mA
Diode Forward Voltage	V _{SD}	-	0.7	1.2	V	V _{GS} = 0V, I _S = 300mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	-	71	-	pF	V _{DS} = 10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	12	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	9.4	-	pF	
Gate Resistance	R _g	-	69	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge	Q _g	-	0.89	-	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 1A
Gate-Source Charge	Q _{gs}	-	0.14	-	nC	
Gate-Drain Charge	Q _{gd}	-	0.16	-	nC	
Turn-On Delay Time	t _{D(on)}	-	4.9	-	ns	V _{DS} = 10V, I _D = 1A V _{GS} = 4.5V, R _G = 6Ω
Turn-On Rise Time	t _r	-	6.9	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	21.7	-	ns	
Turn-Off Fall Time	t _f	-	10.6	-	ns	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm X 25mm square copper plate.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

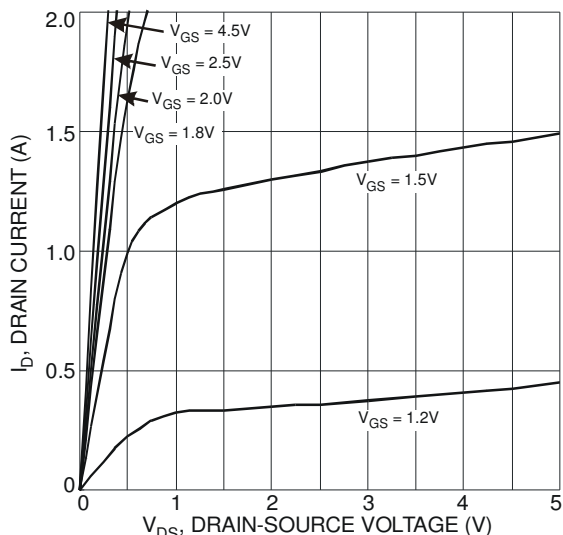


Fig. 1 Typical Output Characteristic

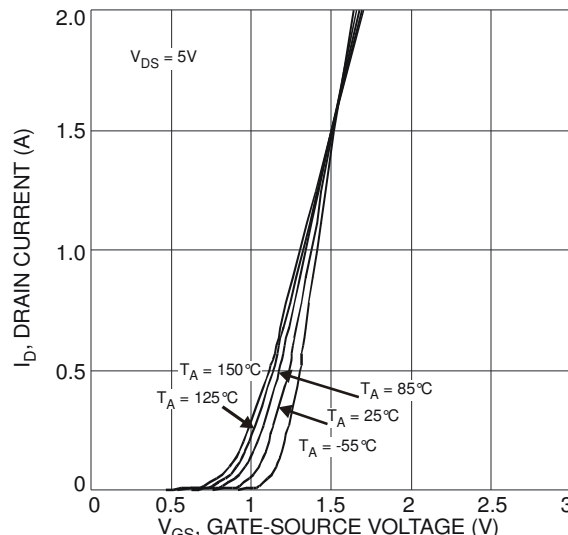


Fig. 2 Typical Transfer Characteristic

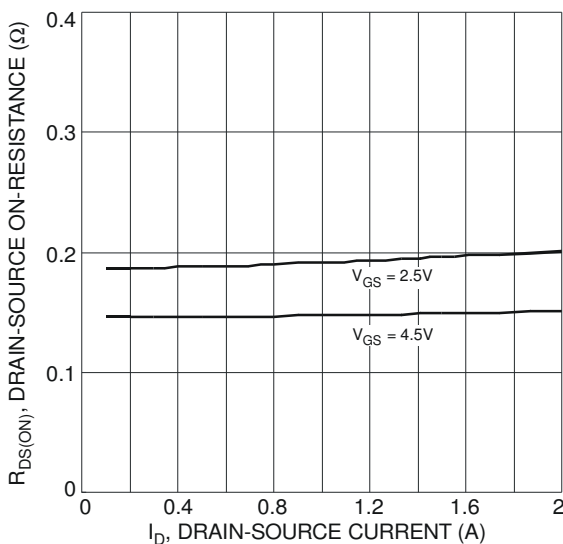


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

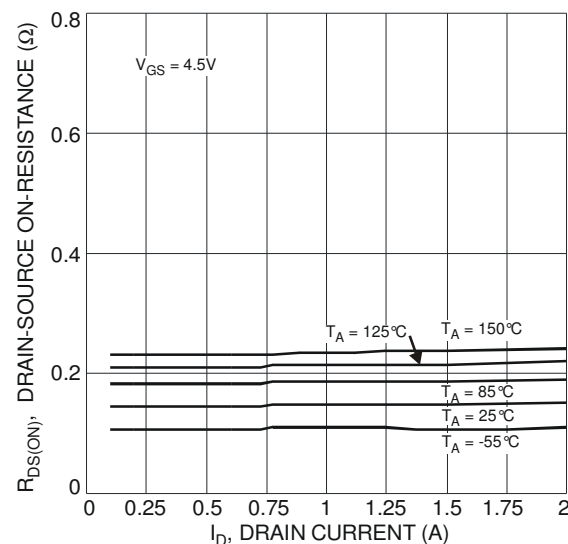


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

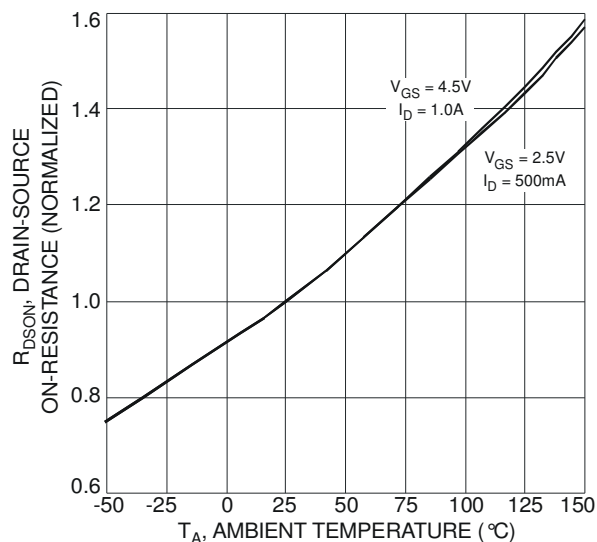


Fig. 5 On-Resistance Variation with Temperature

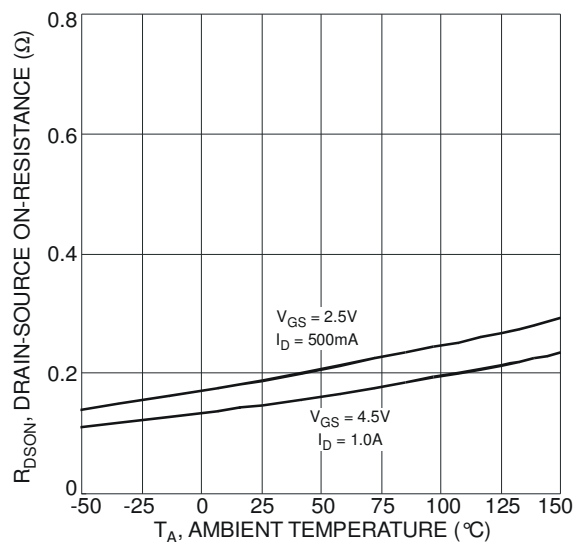


Fig. 6 On-Resistance Variation with Temperature

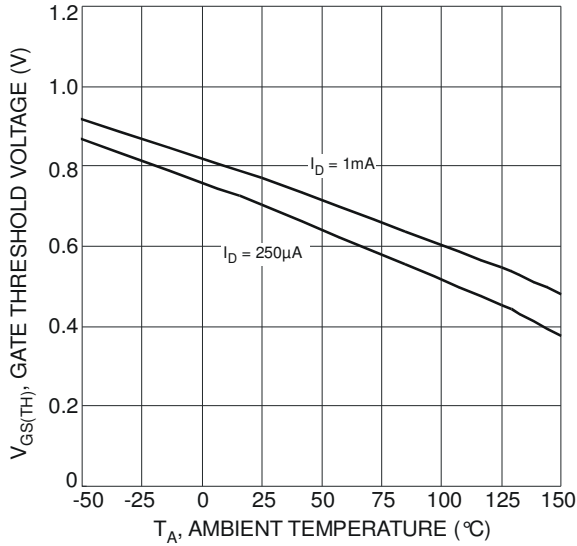


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

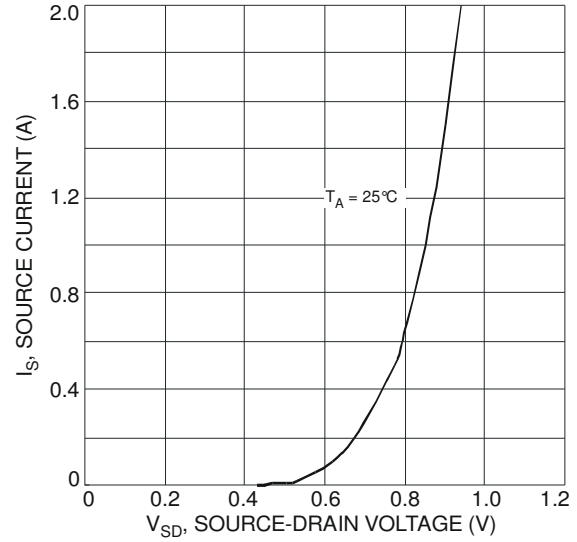


Fig. 8 Diode Forward Voltage vs. Current

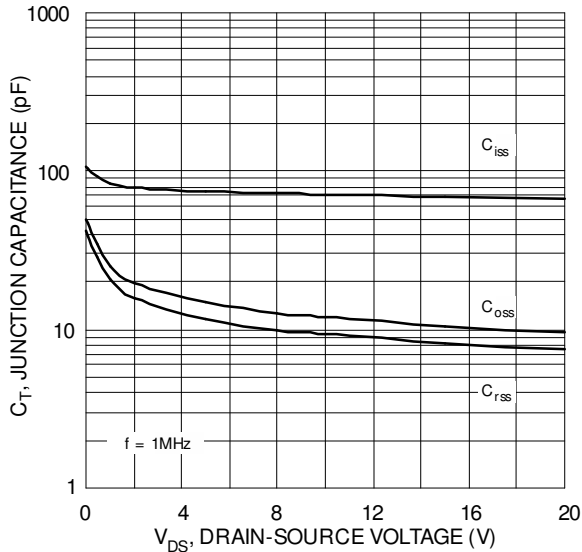


Fig. 9 Typical Junction Capacitance

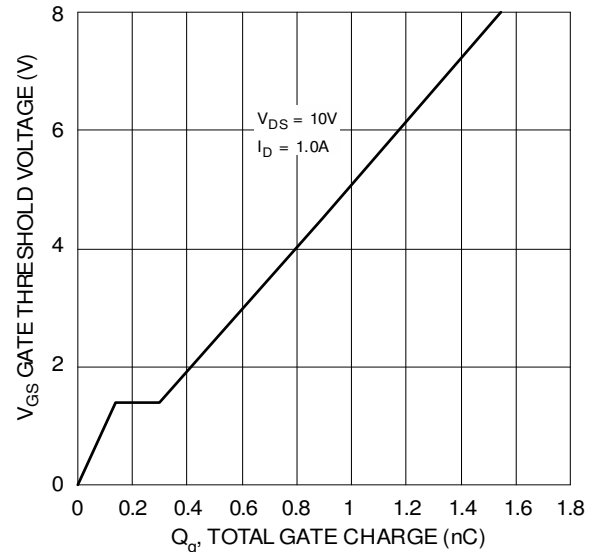


Fig. 10 Gate Charge

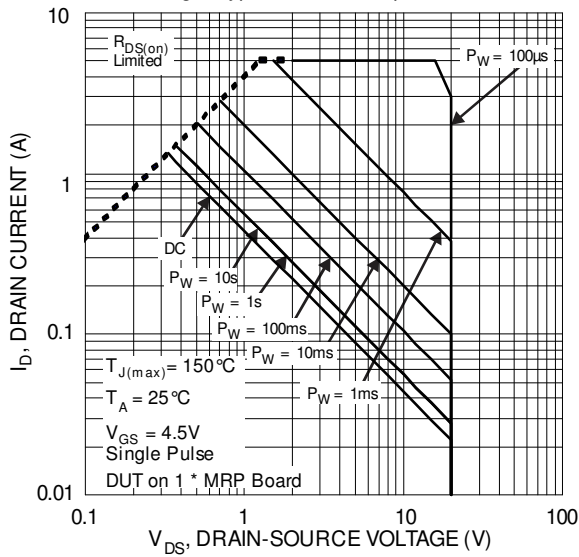
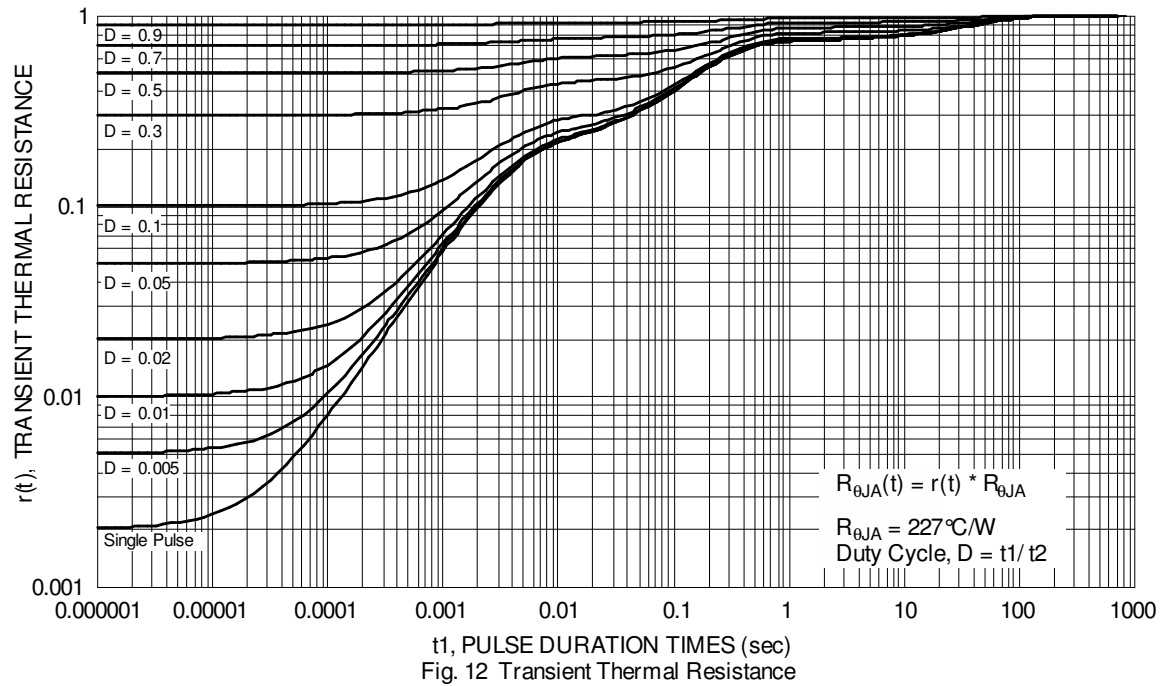
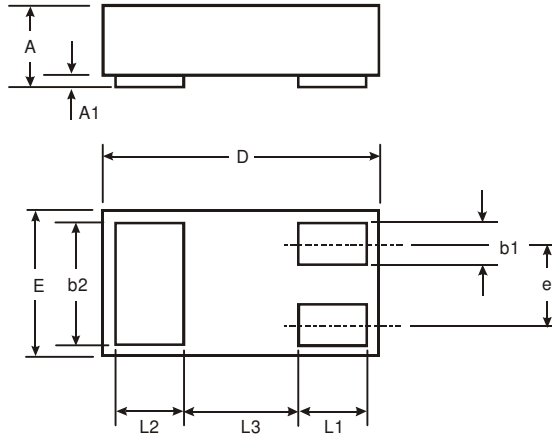


Fig. 11 SOA, Safe Operation Area



Package Outline Dimensions

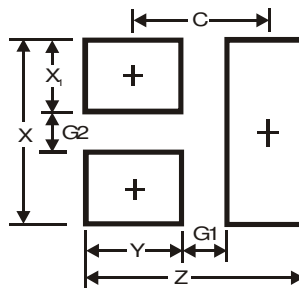
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



X2-DFN1006-3			
Dim	Min	Max	Typ
A	—	0.40	—
A1	0	0.05	0.03
b1	0.10	0.20	0.15
b2	0.45	0.55	0.50
D	0.95	1.05	1.00
E	0.55	0.65	0.60
e	—	—	0.35
L1	0.20	0.30	0.25
L2	0.20	0.30	0.25
L3	—	—	0.40
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
X	0.7
X1	0.25
Y	0.4
C	0.7

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